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(71)Applicant : NIPPON TELEGR & TELEPH CORP  
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(72)Inventor : DOUSEKI TAKAKUNI

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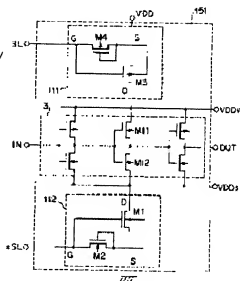
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## (54) MOSFET CIRCUIT

(57)Abstract:

**PROBLEM TO BE SOLVED:** To realize a high speed operation and low power consumption while employing a wide range of a power supply voltage.

**SOLUTION:** A MOSFET circuit 111 (112) being power supply control circuits to control standby/operation is connected between a low threshold voltage CMOS circuit group 3 and a power supply voltage point VDD (ground point). AMOS FET M1 (M3) with a high threshold voltage of the MOSFET circuit 111 (112) receives a back gate bias with a MOS FET M2 (M4) with a low threshold voltage to block a current between a back gate terminal and a gate terminal.



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